

Peak pulse voltage (T _j =25 ; non-repetitive, off-state; FIG.8)	V _{pp}	4	kV
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(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit
I _{GT}	V _D =12V R _L =33Ω	- -	MAX. 10	

J	ST	02	V	-1000	SW
JieJie Microelectronics Co., Ltd.	Triacs				SW:IGT1-3 1000:V _{DRM} /V _{RRM} ≥ 1000V

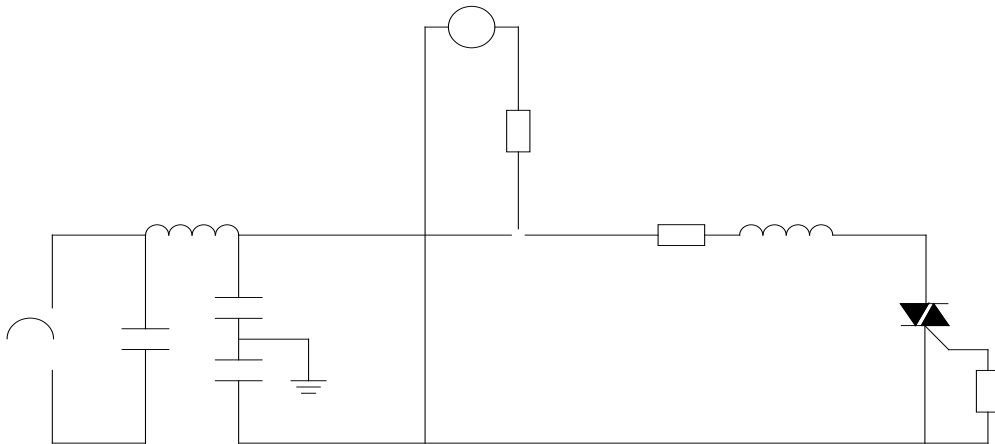
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



JST02V-1000SW

JieJie M

Dimensions

W14.37 ()13I

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